

-	437	((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:27
-	5448	channel near3 hot	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:05
-	9	(channel adj hot) and (tantalum titanium zirconium niobium) adj oxide and aluminum adj oxide	USPAT; US-PGPUB	2003/04/29 14:05
-	6271	sram and (floating adj gate non-volatile nonvolatile)	USPAT; US-PGPUB	2003/10/10 11:27
-	157	(conduction adj band adj offset) not ((tunnel adj barrier barrier adj height) near3 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:06
-	165	(tunnel adj barrier barrier adj height) near3 silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:06
-	1	work adj function near3 silicon adj dioxide	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/29 14:06
-	6	((("4271487") or ("4333166") or ("4760556") or ("5042011") or ("5111427") or ("5153853") or ("5280205") or ("5399516") or ("5418739") or ("5424569") or ("5488587") or ("5497494") or ("5619642") or ("5627785") or ("5796670") or ("5801401") or ("5852306") or ("5870327") or ("5880991") or ("5986932") or ("6009011")).PN.) and sram	USPAT	2003/04/29 14:06
-	40	((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric	USPAT; US-PGPUB	2003/04/29 14:06
-	145	((floating adj gate) and ((257/315,321).CCLS.)) ((floating adj gate) and 257/3\$2.ccls.) not ((floating adj gate) and ((257/315,321).CCLS.))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide	USPAT; US-PGPUB	2003/04/29 14:06
-	1	tunnel adj barrier near3 silicon adj dioxide	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/29 14:06
-	24	((((floating adj gate) and ((257/315,321).CCLS.)) ((floating adj gate) and 257/3\$2.ccls.) not ((floating adj gate) and ((257/315,321).CCLS.))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot	USPAT; US-PGPUB	2003/04/29 14:06
-	21	perovskite near3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:06
-	6	((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:06
-	135	(sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.(365/149,154,185.01,185.08).CCLS.) and @pd>20021203)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/10 11:20
-	33	(channel adj hot) and (tantalum titanium zirconium niobium) adj oxide	USPAT; US-PGPUB	2003/04/29 14:06
-	9	(channel adj hot) and tantalum adj oxide and aluminum adj oxide	USPAT; US-PGPUB	2003/04/29 14:06

-	609	<p>((conduction adj band adj offset) (((tunnel adj barrier barrier adj height) near3 silicon) and ("5606177").PN.)) (channel adj hot adj electron) ((channel adj hot adj electron) and oxide) (((channel adj hot adj electron) and oxide) and tunnel) perovskite ((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) (((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and @pd>20021203) (channel adj hot) (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203) (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate) (channel near3 hot) ((channel adj hot) and (tantalum titanium zirconium niobium) adj oxide and aluminum adj oxide) (sram and (floating adj gate non-volatile nonvolatile)) sram (((US-6141248-\$ or US-6069816-\$).did.) and (insulator insulation insulating gate oxide) ((US-6141248-\$).did.) ((conduction adj band adj offset) not ((tunnel adj barrier barrier adj height) near3 silicon)) (conduction adj band adj offset) ("5606177").PN.) ((US-6141248-\$ or US-6069816-\$).did.) ((tunnel adj barrier barrier adj height) near3 silicon) "1011" (((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric) "1318" (((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)) ((US-6501677-\$ or US-6501692-\$ or US-6504765-\$ or US-6504775-\$ or US-6504786-\$ or US-6504788-\$ or US-6507124-\$ or US-6509616-\$ or US-6510075-\$ or US-6510076-\$ or US-6528817-\$ or US-6528839-\$ or US-6529397-\$ or US-6529399-\$ or US-6529401-\$ or US-6529403-\$ or US-6529407-\$ or US-6529408-\$ or US-6531731-\$ or US-6532169-\$ or US-6534819-\$ or US-6535417-\$ or US-6535442-\$ or US-6535453-\$ or US-6538277-\$ or US-6538338-\$).did. or (US-6542401-\$ or US-6545297-\$ or US-6545311-\$ or US-6545905-\$ or US-6549448-\$ or US-6549449-\$ or US-6549450-\$ or US-6549451-\$ or US-6549452-\$ or US-6549453-\$ or US-6549458-\$ or US-6512245-\$ or US-6512691-\$ or US-6512700-\$ or US-6512718-\$ or US-6515894-\$ or US-6515931-\$ or US-6519176-\$ or US-6519204-\$ or US-6522569-\$ or US-6522582-\$ or US-6522586-\$ or US-6525382-\$ or US-6525962-\$ or US-6525983-\$ or US-6525985-\$ or US-6493255-\$).did. or (US-6493256-\$ or US-6493267-\$ or US-6496887-\$ or US-6501127-\$).did. or (US-20020179960-\$ or US-20020179964-\$ or US-20020180069-\$ or US-20020181273-\$ or US-20020181274-\$ or US-20020185692-\$ or US-20020186579-\$ or US-20020186580-\$ or US-20020186581-\$ or US-20020190343-\$ or US-20020191436-\$ or US-20020195669-\$ or US-20030002328-\$ or US-20030007380-\$ or US-20030007381-\$ or US-20030012049-\$ or US-20030016554-\$ or US-20030021144-\$ or US-20030026124-\$ or US-20030026150-\$ or US-20030038317-\$ or US-20030042553-\$ or US-20030043538-\$ or US-20030043618-\$ or US-20030052371-\$ or US-20030053330-\$).did. or (US-20030058687-\$ or US-20030063485-\$ or US-20030063490-\$ or US-20030067043-\$).did.) ((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203)) ((channel adj hot) and (tantalum titanium zirconium niobium) adj oxide) ((channel adj hot) and tantalum adj oxide and aluminum adj oxide)) and @pd>20030415</p>	<p>USPAT; US-PGPUB; EPO; JPO; IBM_TDB</p>	<p>2003/04/29 14:32</p>
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-	416	(((conduction adj band adj offset) (((tunnel adj barrier barrier adj height) near3 silicon) and ("5606177").PN.)) (channel adj hot adj electron) ((channel adj hot adj electron) and oxide) (((channel adj hot adj electron) and oxide) and tunnel) perovskite ((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) (((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and @pd>20021203) (channel adj hot) (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203) (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate) (channel near3 hot) ((channel adj hot) and (tantalum titanium zirconium niobium) adj oxide and aluminum adj oxide) (sram and (floating adj gate non-volatile nonvolatile)) sram (((US-6141248-\$ or US-6069816-\$).did.) and (insulator insulation insulating gate oxide)) ((US-6141248-\$).did.) ((conduction adj band adj offset) not ((tunnel adj barrier barrier adj height) near3 silicon)) (conduction adj band adj offset) ("5606177").PN.) ((US-6141248-\$ or US-6069816-\$).did.) ((tunnel adj barrier barrier adj height) near3 silicon) "1011" (((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric) "1318" (((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)) ((US-6501677-\$ or US-6501692-\$ or US-6504765-\$ or US-6504775-\$ or US-6504786-\$ or US-6504788-\$ or US-6507124-\$ or US-6509616-\$ or US-6510075-\$ or US-6510076-\$ or US-6528817-\$ or US-6528839-\$ or US-6529397-\$ or US-6529399-\$ or US-6529401-\$ or US-6529403-\$ or US-6529407-\$ or US-6529408-\$ or US-6531731-\$ or US-6532169-\$ or US-6534819-\$ or US-6535417-\$ or US-6535442-\$ or US-6535453-\$ or US-6538277-\$ or US-6538338-\$).did. or (US-6542401-\$ or US-6545297-\$ or US-6545311-\$ or US-6545905-\$ or US-6549448-\$ or US-6549449-\$ or US-6549450-\$ or US-6549451-\$ or US-6549452-\$ or US-6549453-\$ or US-6549458-\$ or US-6512245-\$ or US-6512691-\$ or US-6512700-\$ or US-6512718-\$ or US-6515894-\$ or US-6515931-\$ or US-6519176-\$ or US-6519204-\$ or US-6522569-\$ or US-6522582-\$ or US-6522586-\$ or US-6525382-\$ or US-6525962-\$ or US-6525983-\$ or US-6525985-\$ or US-6493255-\$).did. or (US-6493256-\$ or US-6493267-\$ or US-6496887-\$ or US-6501127-\$).did. or (US-20020179960-\$ or US-20020179964-\$ or US-20020180069-\$ or US-20020181273-\$ or US-20020181274-\$ or US-20020185692-\$ or US-20020186579-\$ or US-20020186580-\$ or US-20020186581-\$ or US-20020190343-\$ or US-20020191436-\$ or US-20020195669-\$ or US-20030002328-\$ or US-20030007380-\$ or US-20030007381-\$ or US-20030012049-\$ or US-20030016554-\$ or US-20030021144-\$ or US-20030026124-\$ or US-20030026150-\$ or US-20030038317-\$ or US-20030042553-\$ or US-20030043538-\$ or US-20030043618-\$ or US-20030052371-\$ or US-20030053330-\$).did. or (US-20030058687-\$ or US-20030063485-\$ or US-20030063490-\$ or US-20030067043-\$).did.) ((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203)) ((channel adj hot) and (tantalum titanium zirconium niobium) adj oxide) ((channel adj hot) and tantalum adj oxide and aluminum adj oxide)) and @pd>20030415) and @pd>20030418	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/29 14:25
-	40	(((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20030415) and @pd>20030418	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/29 14:26
-	117	(sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20030415)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/10 11:21
-	4202	(257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS. and @pd>20030415	USPAT; US-PGPUB	2003/10/10 11:21
-	47	(sram and (floating adj gate non-volatile nonvolatile)) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS. and @pd>20030415) not dram)	USPAT; US-PGPUB	2003/10/10 11:23
-	109	((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20030415)) not ((sram and (floating adj gate non-volatile nonvolatile)) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS. and @pd>20030415) not dram))	USPAT; US-PGPUB	2003/10/10 11:23

-	156	((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20030415)) ((sram and (floating adj gate non-volatile nonvolatile)) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS. and @pd>20030415) not dram))	USPAT; US-PGPUB	2003/10/10 11:23
-	1530	((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and @pd>20030415	USPAT; US-PGPUB	2003/10/10 11:25
-	2008	((conduction adj band adj offset) (((channel adj hot adj electron) and oxide) and tunnel) (((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and @pd>20021203) (channel adj hot) (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate) (channel near3 hot) ((channel adj hot) and (tantalum titanium zirconium niobium) adj oxide and aluminum adj oxide) (sram and (floating adj gate non-volatile nonvolatile)) ((conduction adj band adj offset) not ((tunnel adj barrier barrier adj height) near3 silicon)) ((tunnel adj barrier barrier adj height) near3 silicon) (((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric) (((floating adj gate) and ((257/315,321).CCLS.)) ((floating adj gate) and 257/3\$2.ccls.) not ((floating adj gate) and ((257/315,321).CCLS.))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide) (perovskite near3 gate) ((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203)) ((channel adj hot) and (tantalum titanium zirconium niobium) adj oxide) ((channel adj hot) and tantalum adj oxide and aluminum adj oxide)) and @pd>20030418	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/10 11:26
-	79	sram and ((365/149,154,185.01,185.08).CCLS.) and @pd>20030415	USPAT; US-PGPUB	2003/10/10 11:27
-	79	((365/149,154,185.01,185.08).CCLS.) not dram and @pd>20030415	USPAT; US-PGPUB	2003/10/10 11:27
-	28	conduction adj band adj offset and @pd>20030415	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:27
-	62	((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate and @pd>20030415	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:27
-	1334	sram and (floating adj gate non-volatile nonvolatile) and @pd>20030415	USPAT; US-PGPUB	2003/10/10 11:28
-	612	sram with (floating adj gate non-volatile nonvolatile) and @pd>20030415	USPAT; US-PGPUB	2003/10/10 11:29
-	1	sram with cmos with (floating adj gate non-volatile nonvolatile) and @pd>20030415	USPAT; US-PGPUB	2003/10/10 11:29
-	28	conduction adj band adj offset and @pd>20030415	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:30
-	244	perovskite and @pd>20030415	USPAT	2003/10/10 11:30
-	6	(sram flip-flop flip adj flop) and (perovskite and @pd>20030415)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:31
-	216	((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20030415)) ((sram and (floating adj gate non-volatile nonvolatile)) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS. and @pd>20030415) not dram))) (((365/149,154,185.01,185.08).CCLS.) not dram and @pd>20030415) (sram with cmos with (floating adj gate non-volatile nonvolatile) and @pd>20030415) (sram flip-flop flip adj flop) and (perovskite and @pd>20030415))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 12:00
-	28	floating adj gate with low adj tunnel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 12:01

L Number	Hits	Search Text	DB	Time stamp
-	775	sram and ((365/149,154,185.01,185.08).CCLS.)	USPAT; US-PGPUB	2003/10/10 11:26
-	2128	((365/149,154,185.01,185.08).CCLS.) not dram	USPAT; US-PGPUB	2003/10/10 11:27
-	70	(sram and (floating adj gate non-volatile nonvolatile)) and (((365/149,154,185.01,185.08).CCLS.) not dram)	USPAT; US-PGPUB	2003/10/10 11:22
-	7	"4295150"	USPAT	2002/12/04 16:22
-	10641	floating adj gate	USPAT; US-PGPUB	2002/12/05 11:55
-	1187	(floating adj gate) and ((257/315,321).CCLS.)	USPAT; US-PGPUB	2002/12/04 18:10
-	581	((floating adj gate) and 257/315,321).CCLS.) not ((floating adj gate) and ((257/315,321).CCLS.))) and tunnel	USPAT; US-PGPUB	2002/12/04 18:40
-	47	((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20030415	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/29 14:26
-	159	conduction adj band adj offset	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:30
-	883	channel adj hot adj electron	USPAT; US-PGPUB	2003/04/29 14:01
-	767	(channel adj hot adj electron) and oxide	USPAT; US-PGPUB	2003/04/29 14:02
-	528	((channel adj hot adj electron) and oxide) and tunnel	USPAT; US-PGPUB	2003/04/29 14:02
-	148375	sram flip-flop flip adj flop	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 11:30
-	134957	floating adj gate non-volatile nonvolatile	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:02
-	282896	work adj function near3 silicon dioxide	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/29 14:03
-	4296	perovskite	USPAT	2003/10/10 11:30
-	9715	(sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/29 14:03
-	1316	((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and @pd>20021203	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/29 14:03
-	2025	channel adj hot	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:04
-	491	((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/04/29 14:04